MSKSEMI 美森科













ESD

Т

TSS

MOV

GDT

PIFD

1N4001-1N4007

Product specification





FEATURES

- Glass passivated device
- Ideal for surface mouted applications
- Low reverse leakage
- Metallurgically bonded construction
- High temperature soldering guaranteed:
 250 C/10 seconds,0.375"(9.5mm) lead length,
 5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: JEDEC SOD-123FL molded plastic body over passivated chip

Terminals: Solderable per MIL-STD-750,

Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any

Weight: 0.0007 ounce, 0.02 grams

Reference News

PACKAGE OUTLINE	Circuit	PINNING		
		PIN	DESCRIPTION	
	1	1	Cathode	
1 SOD-123FL		2	Anode	

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25℃ ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Catalog Numb	per	SYMBOLS	1N4001 A1	1N4002 A2	1N4003 A3	1N4004 A4	1N4005 A5	1N4006 A6	1N4007 A7	UNITS
Maximum repetitive peak reverse ve	oltage	VRRM	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage		V _{RMS}	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage		VDC	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified Ta=65 C (NOTE 1)	current at	l(AV)	1.0			Amp				
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) TL=25°C LESM 25.0			Amps							
Maximum instantaneous forward voltage at 1.0A		VF	1.1						Volts	
Maximum DC reverse current at rated DC blocking voltage	Ta=25℃ Ta=125℃	lR	10.0 50.0			μA				
Typical junction capacitance (NOTE	2)	Сл				4				pF
rpical thermal resistance (NOTE 3) Reja 180			K/W							
Operating junction and storage tem	perature range	T _J ,T _{STG}	тв -55 to +150		$^{\circ}$ C					

Note: 1.Averaged over any 20ms period.

2.Measured at 1MHz and applied reverse voltage of 4.0V D.C.

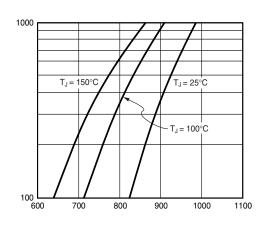
^{3.} Thermal resistance from junction to ambient at 0.375" (9.5mm)lead length, P.C.B. mounted



RATINGS AND CHARACTERISTIC CURVES 1N4001 THRU 1N4007

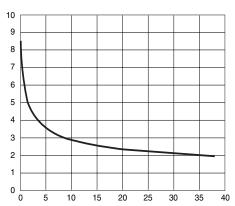
FIG.1 - TYPICAL FORWARD CHARACTERISTIC

INSTANTANEOUS FORWARD CURRENT m AMPERES



INSTANTANEOUS FORWARD VOLTAGE, mV

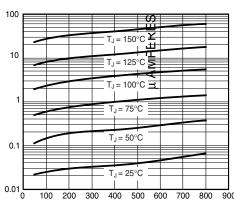
FIG.2 - TYPICAL JUNCTION CAPACITANCE



REVERSE VOLTAGE, VOLTS

INSTANTANEOUS REVERSE CURRENT



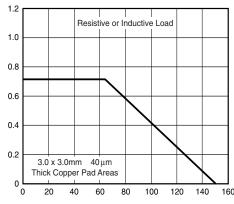


INSTANTANEOUS REVERSE VOLTAGE,V

AVERAGE FORWARD CURRENT, AMPERES

CAPACITANCE, pF

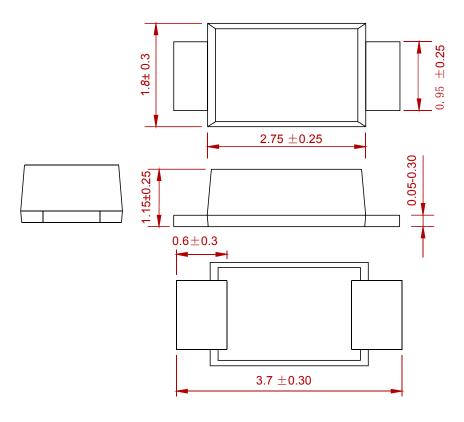
FIG.4 – FORWARD DERATING CURVE



AMBIENT TEMPERATUREC

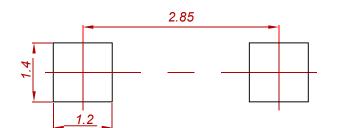


PACKAGE MECHANICAL DATA



Dimensions in millimeters

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
1N4001-1N4007	SOD-123FL	3000



Attention

- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer'sproducts or equipment.
- MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possiblethat these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuitsfor safedesign, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.